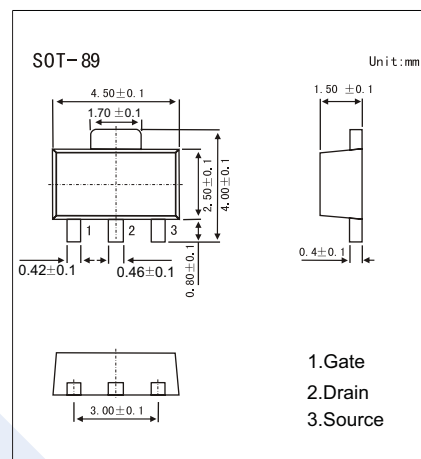
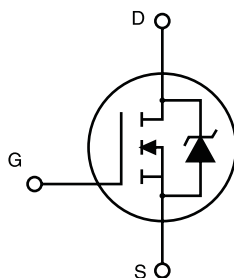


N-Channel Power MOSFET

KI1N60

■ Features

- $V_{DS}(V) = 600V$
- $I_D = 1A$
- $R_{DS(ON)} < 10.5\Omega$ ($V_{GS} = 10V$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current	$T_C=25^\circ C$	1	A
	$T_C=100^\circ C$	0.7	
Pulsed Drain Current	I_{DM}	4	
Power Dissipation	$T_C=25^\circ C$	3	W
Single Pulse Avalanche Energy	E_{AS}	30	mJ
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250\mu A$, $V_{GS}=0V$	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V$, $V_{GS}=0V$, $T_C=25^\circ C$			1	μA
		$V_{DS}=480V$, $V_{GS}=0V$, $T_C=125^\circ C$			100	
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 30V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$, $I_D=0.5A$			10.5	Ω
Input Capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=25V$, $f=1MHz$		150		pF
Output Capacitance	C_{oss}			25		
Reverse Transfer Capacitance	C_{rss}			4		
Diode Forward Voltage	V_{SD}	$I_S=1A$, $V_{GS}=0V$			1.5	V

Note: Pulse test $t_p \leq 300\mu s$, $\delta \leq 2\%$

■ Marking

Marking	1N60
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N-Channel Power MOSFET

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■ Typical Characteristics

Figure 1. Typical Output Characteristics

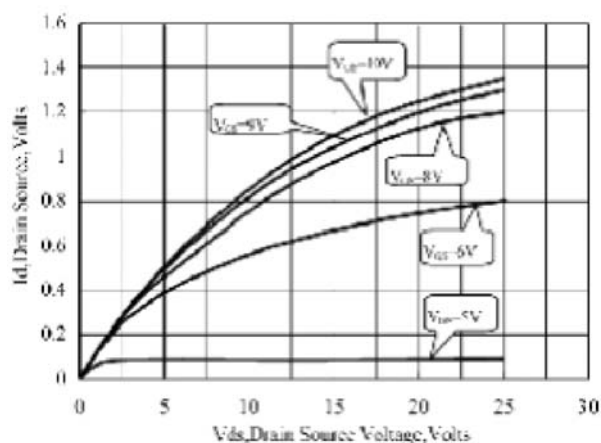


Figure 2. On-Resistance vs. Gate Voltage

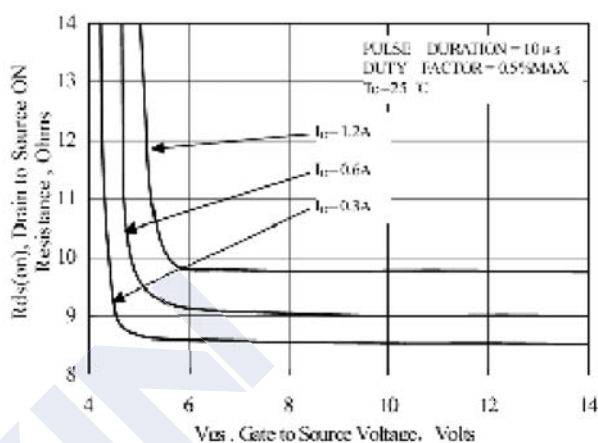


Figure 3. On-Resistance vs. Drain Current

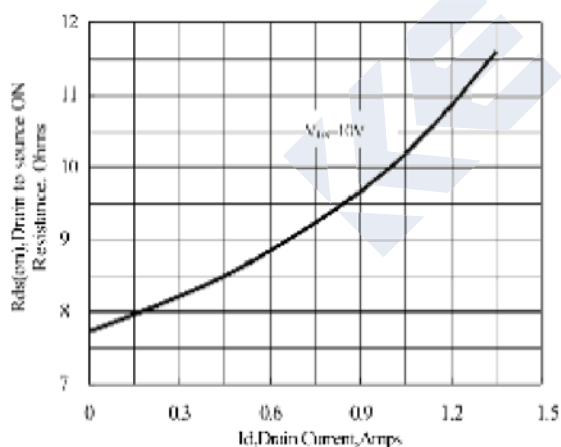


Figure 4. On-Resistance Variation with Temperature

